Form PTO 1449 (Modified)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY DOCKET NO. 243479US0	SERIAL NO. New Application
LIST OF REFERENCES CITED BY APPLICANT		APPLICANT Hidetoshi FUJIMOTO	
		FILING DATE Herewtih	GROUP

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES	TRANSLATION NO
	AO					
	AP					
	AQ					
	AR					
	AS					
	AT					
	AU					
	AV					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

	AW	N. Watanabe, et al., "Metamorphic InP/InGaAs heterojunction bipolar transistors grown on GaAs substrate by MOCVD" Extended Abstracts (The 62nd Autumn Meeting, 2001) THE JAPAN SOCIETY OF APPLIED PHYSICS, No. 3, pg 1069
	AX	Y. Takano, et al., "Two-step Growth of INP on GaAs Substrates by Organometallic Vapor Phase Epitaxy", BULLETIN OF THE RESEARCH INSTITUTE OF ELECTRONICS, Shizuoka University, Vol. 30, No. 3, 1995, pgs. 65-67
	AY	H. Horikawa, et al., "Heteroepitaxial growth of INP on GaAs substrate by low-pressure metalorganic vapor phase epitaxy", APPL. PHYS. LETT., Vol. 53, No. 5, 1988, pgs 397-399
	AZ	

☐ Additional References sheet(s) attached

Examiner [signature]

Date Considered 4/20/05

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